What is claimed is:

1. A method for inspecting crystal quality of a polysilicon film, comprising the steps of:

providing a substrate covered by a polysilicon layer;

irradiating a light beam having a predetermined wavelength through a beam splitter to separate into a first light beam and a second light beam, for irradiating the polysilicon layer;

detecting the light intensity of the first light beam and the light intensity of the second light beam reflected from the polysilicon layer to achieve a light intensity ratio; and

monitoring crystal quality of the polysilicon layer by the light intensity ratio.

2. The method as claimed in claim 1, wherein the substrate is a glass substrate.

3. The method as claimed in claim 1, wherein the light beam is a laser beam and the predetermined wavelength is about 266~316 nm.

4. The method as claimed in claim 3, wherein a split ratio of the first light beam to the second light beam is 30~40%:70~60%.

5. An apparatus for inspecting crystal quality of a polysilicon film, comprising:

a probe light beam having a predetermined wavelength for irradiating a polysilicon layer formed on a substrate;

a beam splitter for receiving the probe light beam to separate into a first light beam and a second light beam, which is used for irradiating the polysilicon layer;

a first detecting device for detecting the light intensity of the first light beam; and

a second detecting device for detecting the light intensity of the second light beam reflected from the polysilicon layer.

6. The apparatus as claimed in claim 5, further comprising a controlling unit coupled between the first and second detecting devices to monitor crystal quality of the polysilicon layer by a light intensity ratio of the first light beam to the second light beam reflected from the polysilicon layer.

7. The apparatus as claimed in claim 5, wherein the probe light beam is a laser beam and the predetermined wavelength is about 266~316 nm.

8. The apparatus as claimed in claim 5, wherein the substrate is a glass substrate.

9. The apparatus as claimed in claim 5, wherein a split ratio of the first light beam to the second light beam is 30~40%:70~60%.

10. A method for controlling crystal quality of a polysilicon film, comprising the steps of:

providing a first substrate covered by a first amorphous silicon layer;

annealing the first amorphous silicon layer by a laser beam with different first predetermined laser energy densities to form a plurality of polysilicon regions therein;

irradiating a probe light beam having a predetermined wavelength through a beam splitter to separate into a first light beam and a second light beam, for irradiating the polysilicon regions;

detecting the light intensity of the first light beam and the light intensity of the second light beam reflected from each polysilicon region to achieve a plurality of light intensity ratios;

determining a second predetermined laser energy density by the light intensity ratios;

providing a second substrate covered by a second amorphous silicon layer; and

annealing the second amorphous silicon layer by the laser beam with the second predetermined laser energy density to form a polysilicon layer on the second substrate.

11. The method as claimed in claim 10, wherein the first and second substrates are glass substrates.

12. The method as claimed in claim 10, wherein the laser beam is an excimer laser beam.

13. The method as claimed in claim 12, wherein the first predetermined laser energy densities are about 300~500 mJ/cm^2.

14. The method as claimed in claim 10, wherein the probe light beam is a laser beam and the predetermined wavelength is about 266~316 nm.

15. The method as claimed in claim 10, wherein a split ratio of the first light beam to the second light beam is 30~40%:70~60%.

16. The method as claimed in claim 10, wherein the second predetermined laser energy density is one of the first laser energy densities which can form the polysilicon layer with the largest grain size.